

# **CFB0301**

High Dynamic Range Low-Noise GaAs FET



### **Product Specifications** June 2002

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# **High Dynamic Range Low-Noise GaAs FET**

Fе	atures
	Low-Noise Figure from 0.8 to 2.0 GHz
	High Gain
	<b>High Intercept Point</b>
	Highly Stable
	Easily Matched to $50\Omega$

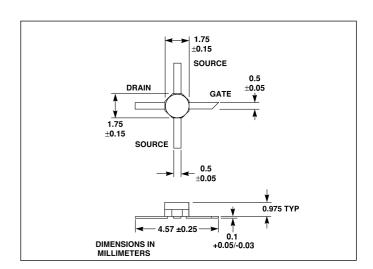
☐ 70 mil Package

### **Applications**

- **□** Cellular Base Stations
- **□** PCS Base Stations
- ☐ Industrial Data Networks

#### **Description**

Celeritek's CFB0301 is a high performance GaAs MESFET with 600 µm gate width and 0.25 µm gate length. The low noise figure and high intercept point of this device makes it well suited for use as the low-noise amplifier of the



base station receiver in PCS, Japanese PHS, AMPS, GSM and other communications systems. The CFB0301 is in an industry-standard 70 mil package. It is surface mountable and available in tape and reel.

#### **Electrical Specifications** (TA = 25°C, 2 GHz)

Parameters	Conditions	Min	Тур	Standard Deviation <sup>4</sup>	Max	Units
$\overline{V_d} = 2V, I_d = 25 \text{ mA}$			7,			
Noise Figure <sup>2</sup>			0.6			dB
Associated Gain <sup>2</sup>	@ Noise Figure		16			dB
Noise Figure <sup>2</sup> Associated Gain <sup>2</sup> Pout <sup>1</sup> , 3	P <sub>-1</sub>		15.0			dBm
$\frac{\frac{1}{1} \frac{1}{1} \frac{3}{3}}{\frac{1}{1} \frac{3}{1}}$	+5 dBm P <sub>OUT</sub> /Tone		24			dBm
$I_d^3$	@ P <sub>-1</sub>		35			mA
$\overline{V_d} = 4V, I_d = 30 \text{ mA}$	•					
Noise Figure <sup>2</sup>			0.7			dB
Associated Gain <sup>2</sup>	@ Noise Figure		17			dB
P <sub>out</sub> 1, 3	P <sub>-1</sub>		20.5			dBm
$IP_3$ <sup>3</sup>	+5 dBm P <sub>OUT</sub> /Tone		30			dBm
Pout 1, 3 IP3 3 Id 3	@ P <sub>-1</sub>		56			mA
$\overline{V_d = 4V, I_d = 70 \text{ mA}}$						
Noise Figure <sup>2</sup>			0.8	0.08	0.9	dB
Associated Gain <sup>2</sup>	@ Noise Figure	16	17	0.4		dB
P <sub>out</sub> 1, 3	P <sub>-1</sub>	20	21	0.4		dBm
$\frac{\overline{\text{IP}_3}^3}{\overline{\text{I}_d}^3}$	+5 dBm P <sub>OUT</sub> /Tone	32	34	0.9		dBm
$I_d^3$	@ P <sub>-1</sub>		77			mA
Transconductance	$V_{ds} = 2 \text{ V}, V_{gs} = 0 \text{ V}$	70	140			mho
Saturated Drain Current	$V_{ds} = 2 \text{ V}, V_{gs} = 0 \text{ V}$	120	150		180	mA
Pinchoff Voltages	$V_{ds} = 2 \text{ V}, I_{ds} = 1 \text{ mA}$	-2.5	-1.3		-0.5	V
Thermal Resistance	@ T <sub>case</sub> = 150°C liquid crystal test		200			°C/W

Notes: 1. @  $T_{case} = 25$ °C. Derate 5 mW/°C for  $T_{case} > 25$ °C. 2. Input matched for low noise.

- 3. Matched for power transfer.

4. Standard deviation based on 10 wafers randomly selected and is provided as an estimate of the distribution only. Trademarks are the property of their respected owners.

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# **Typical Noise Parameters** $(V_{ds} = 4 \text{ V}, I_{ds} = 30 \text{ mA})$

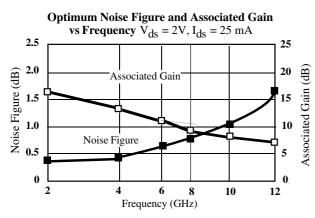
Frequency	F <sub>min</sub> <sup>1</sup>	Gamn		
(GHz)	(dB)	Mag	Ang	Rn/50
0.8	0.4	0.6	27	0.19
1.0	0.4	0.6	29	0.17
1.2	0.4	0.6	32	0.18
1.4	0.4	0.6	35	0.18
1.6	0.4	0.5	38	0.17
1.8	0.4	0.5	41	0.16
2.0	0.5	0.5	45	0.15
2.2	0.5	0.5	49	0.15
2.4	0.5	0.5	54	0.14
2.6	0.5	0.5	60	0.13

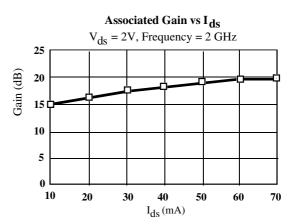
Note: 1. Fmin values reflect the circuit losses in the test fixture when matched to optimum noise figure.

### **Absolute Maximum Ratings**

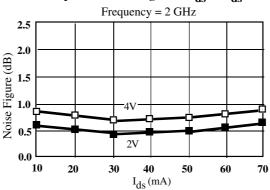
Parameter	Symbol	Rating
Drain-Source Voltage	V <sub>ds</sub>	+8V
Gate-Source Voltage	17	-5V
Drain Current	$I_{\underline{d}s}^{v_{gs}}$	Idss
Continuous Dissipation <sup>1</sup>	Pt	750 mW
Channel Temperature	Tch	175°C
Storage Temperature	Tstg	-65°C to $+150$ °C

# **Typical Performance**





### Optimum Noise Figure vs I $_{ds}$ & V $_{ds}$



**Typical Scattering Parameters** (TA = 25°C,  $V_{DS} = 2$  V,  $I_{DS} = 25$  mA)

			20	20 20				
Frequency	s <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
(ĠHz)	Mag	Ang	Mag (dB)	Ang	MAG (dB)	ANG	MAG	ANG
0.5	0.98	-20	7.17	161	0.02	78	0.42	-11
1.0	0.94	-40	6.90	148	0.03	70	0.41	-24
2.0	0.85	-76	6.00	119	0.05	52	0.36	-46
3.0	0.76	-108	5.00	95	0.07	38	0.32	-65
4.0	0.70	-130	4.30	75	0.08	30	0.30	-75
5.0	0.64	-150	3.83	55	0.09	20	0.27	-85





## **Product Specifications - June 2002**

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#### **Test Circuit** Evaluation Board Schematic

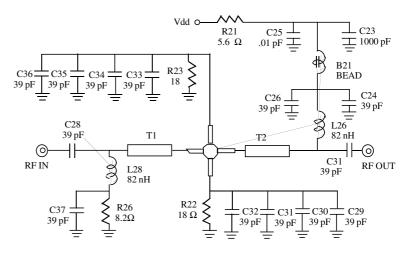
Evaluation Board Substrate:

ER = 4.65

Thickness = 0.036

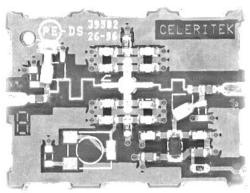
Transmission Lines (Dimensions in mm.):

T1: 0.203 (W) x 11.55 (L) T2: 0.203 (W) x 5.05 (L)



#### **PB-CFB0301 Evaluation Board**

(SMA Connectors not shown)



#### **Evaluation Board Parts List**

Item	Reference Designator	Description	Quantity	Manufacturer	Part Number
1	B21	Chip ferrite bead 0805	1	World Products	HB-1H2012-260JT
2	C23	Capacitor, 1000pF, 0603	1	Rohm	MCH185A102JK
3	C21, C24, C26, C28-C37	Capacitor, 39pF, 0603	13	Rohm	MCH185A039JK
4	C25	Capacitor, 0.01µF, 0603	1	Rohm	MCH185A103JK
5	L26, L28	Inductor, 82nH, INDA5T-3	2	Toko	LL2012-F8NK
6	R21	Resistor, 5.6 Ohm, 0603	1	Dale	RCWP575 560
7	R22, R23	Resistor, 18 Ohm, 0603	2	Dale	RCWP575 181
8	R26	Resistor, 8.2 Ohm, 0603	1	Dale	RCWP575 820

#### **Ordering Information**

The CFB0301GaAs FET is available in tape and reel. An evaluation board is also available. Ordering part numbers are listed.

Part Number for Ordering Function Package

CFB0301 Low-Noise high dynamic range FET 70 mil package

CFB0301-000T Low-Noise high dynamic range FET 70 mil package in tape and reel

PB-CFB0301 Evaluation Board

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